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November 2013

#### **FDP036N10A**

# N-Channel PowerTrench<sup>®</sup> MOSFET 100 V, 214 A, 3.6 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 3.2  $m\Omega$  ( Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 75 A
- · Fast Switching Speed
- Low Gate Charge, Q<sub>G</sub> = 89 nC (Typ.)
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- · High Power and Current Handling Capability
- · RoHS Compliant

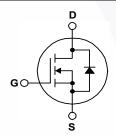
#### Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

#### **Applications**

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Micro Solar Inverter





#### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

	9	o .		
Symbol		Parameter	FDP036N10A	Unit
V <sub>DSS</sub>	Drain to Source Voltage		100	V
V <sub>GSS</sub>	Gate to Source Voltage		±20	V
		- Continuous (T <sub>C</sub> = 25°C, Silicon Limited)	214*	
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 100°C, Silicon Limited)	151*	Α
		- Continuous (T <sub>C</sub> = 25°C, Package Limited)	120	
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	856	Α
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		658	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
D	Power Dissipation	$(T_C = 25^{\circ}C)$	333	W
$P_{D}$	Power Dissipation	- Derate Above 25°C	2.22	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temperature	for Soldering, 1/8" from Case for 5 Seconds	300	°C

<sup>\*</sup>Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

#### **Thermal Characteristics**

Symbol	Parameter	FDP036N10A	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max.	0.45	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	C/VV

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP036N10A	FDP036N10A	TO-220	Tube	N/A	N/A	50 units

#### **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ}C$	100	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 μA, Referenced to 25°C	-	0.03	-	V/°C
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	-	-	1	μA
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V	-	-	±100	nA

#### On Characteristics

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.0	3.0	4.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 75 A	-	3.2	3.6	mΩ
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 75 A	-	167	-	S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		5485	7295	pF
C <sub>oss</sub>	Output Capacitance			2430	3230	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			210	315	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V		- \	89	116	nC
$Q_{gs}$	Gate to Source Gate Charge	$V_{DS} = 80 \text{ V}, I_{D} = 75 \text{ A},$		24	-	nC
Q <sub>gs2</sub>	Gate Charge Threshold to Plateau	V <sub>GS</sub> = 10 V	-	8	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note 4)	-	25	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1.2	-	Ω

#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	22	54	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 50 \text{ V}, I_{D} = 75 \text{ A},$	-	54	118	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$	-	37	84	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	-	11	32	ns

#### **Drain-Source Diode Characteristics**

Is	Maximum Continuous Drain to Source Diode Forward Current			-	214	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	856	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A	-	-	1.25	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A,	-	72	93.6	ns
$Q_{rr}$	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	129	-	nC

#### Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. Starting  $T_J$  = 25°C, L = 1 mH,  $I_{AS}$  = 36.3 A.
- 3. I\_{SD}  $\leq$  75 A, di/dt  $\leq$  200 A/µs, V\_DD  $\leq$  BV\_DSS, starting T\_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

### **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

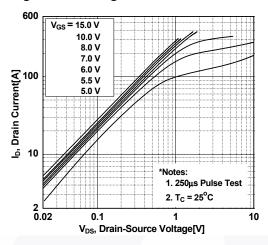


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

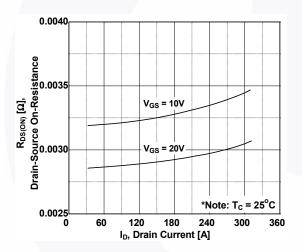


Figure 5. Capacitance Characteristics

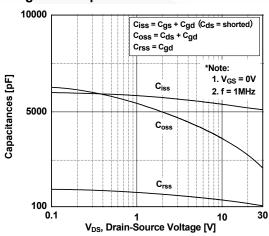


Figure 2. Transfer Characteristics

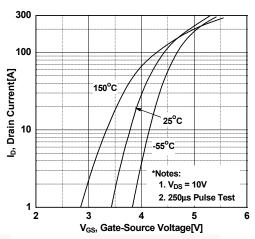


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

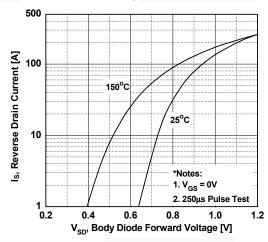
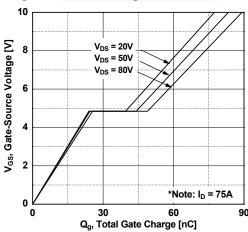


Figure 6. Gate Charge Characteristics



#### **Typical Performance Characteristics**

Figure 7. Breakdown Voltage Variation vs. Temperature

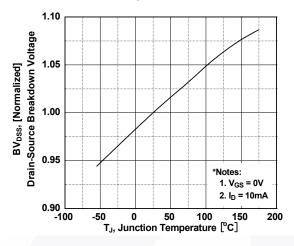


Figure 9. Maximum Safe Operating Area

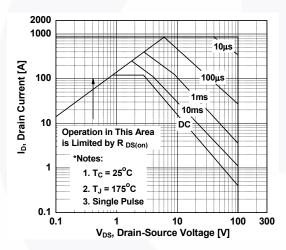


Figure 8. On-Resistance Variation vs. Temperature

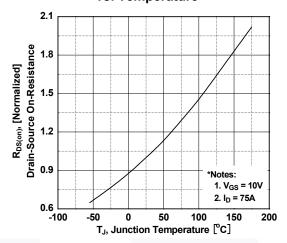


Figure 10. Maximum Drain Current vs. Case Temperature

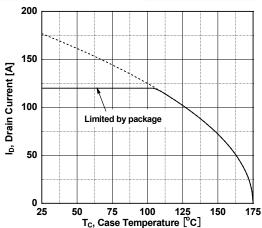
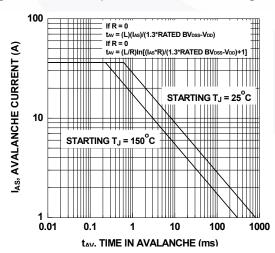
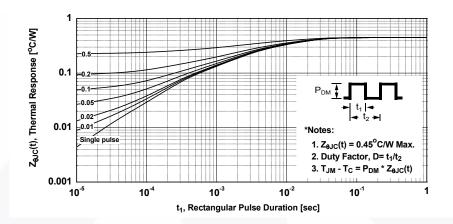


Figure 11. Unclamped Inductive Switching Capability



### **Typical Performance Characteristics**

Figure 12. Transient Thermal Response Curve



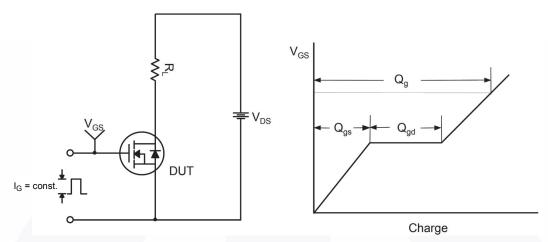


Figure 13. Gate Charge Test Circuit & Waveform

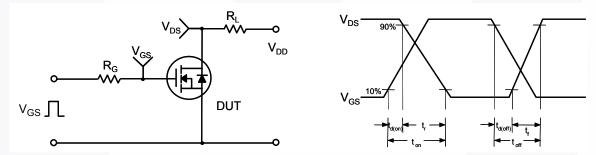


Figure 14. Resistive Switching Test Circuit & Waveforms

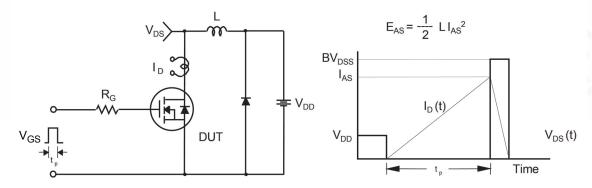


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

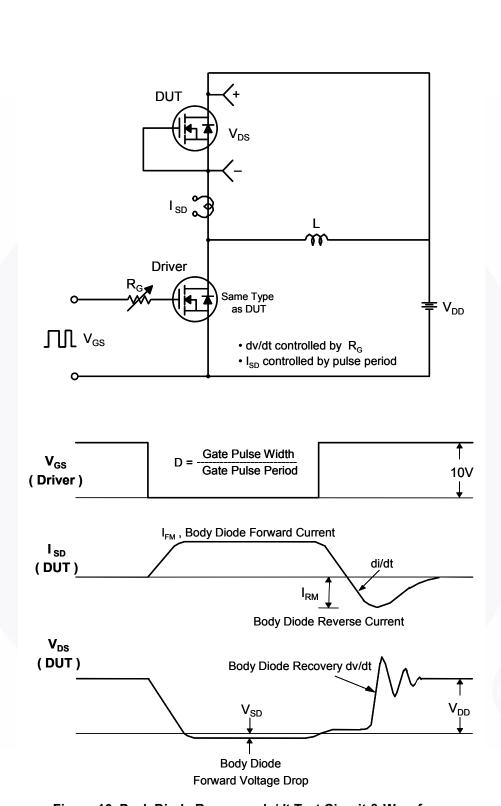


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

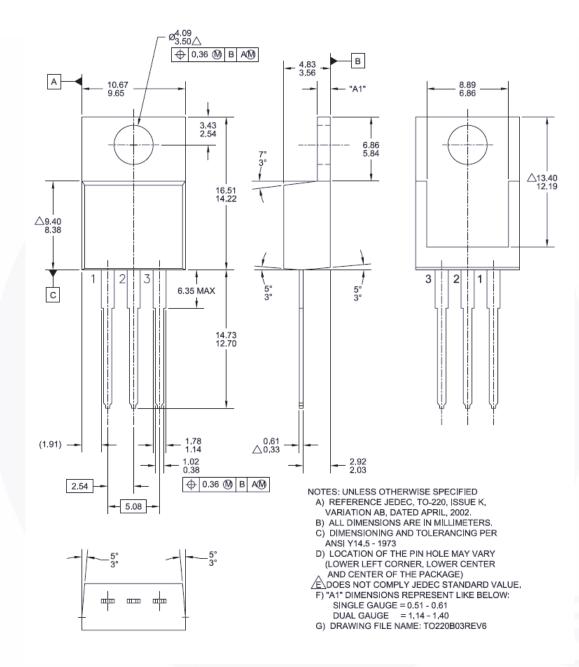


Figure 17. TO-220, Molded, 3-Lead, Jedec Variation AB

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